

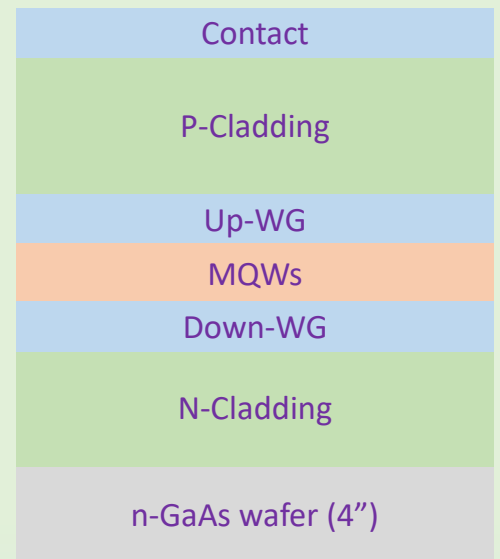
1064 nm FP LD epiwafers



We offer a variety of standard and customized GaAs based FP LD epiwafers for pumping, sensing, luminescence, and other applications.

Key Features

- High uniformity PL wavelength
- Special design of high gain MQWs
- Output power up to 20~200 mW (with different device structure)
- High reliability
- Low power consumption
- high strain InGaAs wells
- Customized lasing wavelength

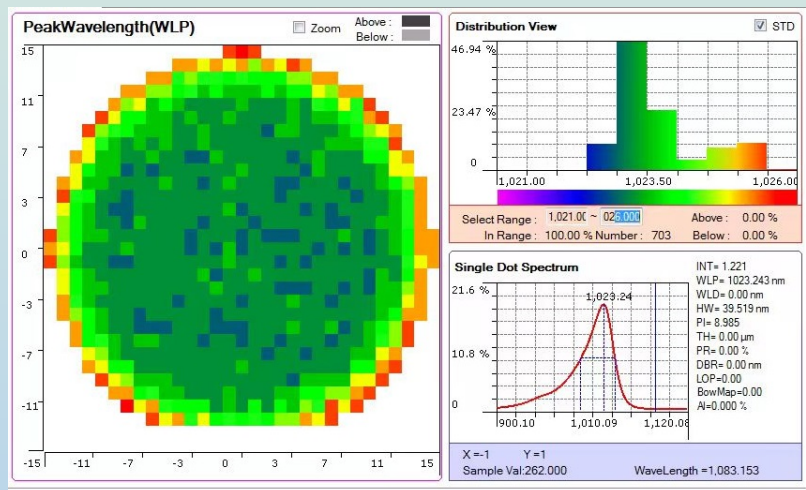


Key Epi-Structure

Default tolerances

Mole fraction	PL (nm)	Thickness (nm)	ECV (cm ⁻³)
±0.05	±8	±5%	±30%

PL Mapping Instance



PIV & Spectrum instance

